NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI AVD0.5S** is Designed for Class A, DME/TACAN Applications up to 1150 MHz.

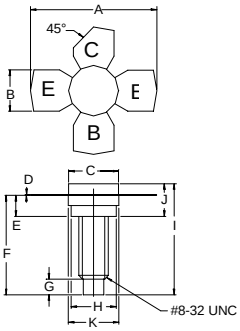
FEATURES:

- Class A Operation
- P_G = 10 dB at 0.5 W/1150 MHz
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	300 mA
V_{CE}	20 V
P_{DISS}	--- W
T_J	-65 ^{O}C to +200 ^{O}C
T_{STG}	-65 ^{O}C to +150 ^{O}C
θ_{JC}	35.0 ^{O}C/W

PACKAGE STYLE .280 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 /5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 1.0 mA	50			V
BV_{CEO}	I_C = 5.0 mA	20			V
BV_{EBO}	I_E = 1.0 mA	3.5			V
I_{CES}	V_{CE} = 28 V			1.0	mA
h_{FE}	V_{CE} = 5.0 V I_C = 100 mA	15		120	---
P_G	V_{CC} = 12.5 V P_{OUT} = 0.5 W f = 1025 - 1150 MHz	10			dB